HALOGEN

FREE

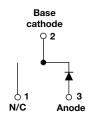


Vishay High Power Products

HEXFRED®

Ultrafast Soft Recovery Diode, 8 A





PRODUCT SUMMARY						
V_{R}	1200 V					
V _F at 8 A at 25 °C	3.3 V					
I _{F(AV)}	8 A					
t _{rr} (typical)	28 ns					
T _J (maximum)	150 °C					
Q _{rr} (typical)	140 nC					
dl _{(rec)M} /dt (typical) at 125 °C	85 A/µs					
I _{RRM} (typical)	4.5 A					

FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Halogen-free according to IEC 61249-2-21 definition
- Compliant to RoHS directive 2002/95/EC
- AEC-Q101 qualified

BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA08TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		1200	V			
Maximum continuous forward current	I _F	T _C = 100 °C	8				
Single pulse forward current	I _{FSM}		130	Α			
Maximum repetitive forward current	I _{FRM}		32				
Mayimum naugudianination	В	T _C = 25 °C	73.5	W			
Maximum power dissipation	P _D	T _C = 100 °C	29	VV			
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C			

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VS-HFA08TB120SPbF

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	V _{BR} I _R = 100 μA		-	-		
		I _F = 8.0 A	-	2.6	3.3	V	
Maximum forward voltage	V_{FM}	I _F = 16 A	-	3.4	4.3		
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1		
Maximum reverse	,	V _R = V _R rated	-	0.31	10		
leakage current		$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	-	135	1000	μA	
Junction capacitance	C _T	V _R = 200 V	-	11	20	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0		-	nH		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	I _F = 1.0 A, dI _F /dt = 200 A/μs, V _R = 30 V		28	-	
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	63	95	ns A
	t _{rr2}	T _J = 125 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	106	160	
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	
	I _{RRM2}	T _J = 125 °C		-	6.2	11	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	140	380	
	Q _{rr2}	T _J = 125 °C		-	335	880	110
Peak rate of fall of recovery current during t _b	dI _{(rec)M} /dt1	T _J = 25 °C		-	133	=	- A/µs
	dI _{(rec)M} /dt2	T _J = 125 °C		-	85	-	- Αν μδ

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. N			MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	1.7	K/W	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount		-	40	N/W	
Weight			-	2.0	-	g	
weignt			-	0.07	-	oz.	
Marking device		Case style D ² PAK	HFA08TB120S				

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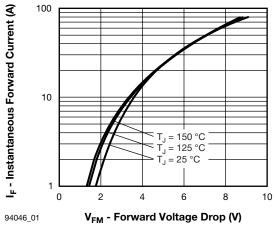


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I_R - Reverse Current (µA) = 125 °C 100 10 0.1 0.01 300 1200

Fig. 1 - Maximum Forward Voltage Drop Characteristics

V_R - Reverse Voltage (V) Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

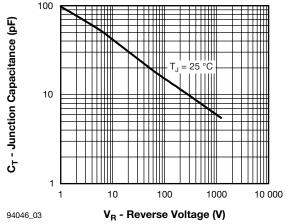


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

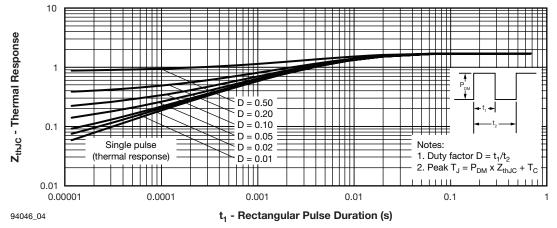


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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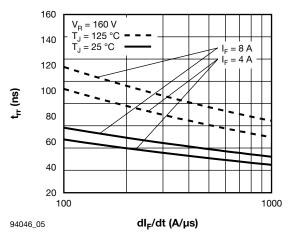


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

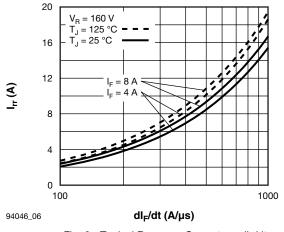


Fig. 6 - Typical Recovery Current vs. dI_F/dt

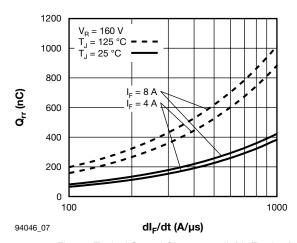


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

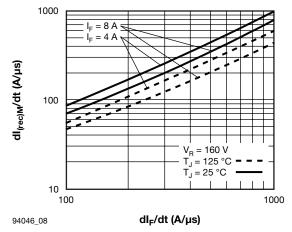


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

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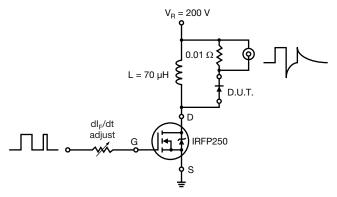
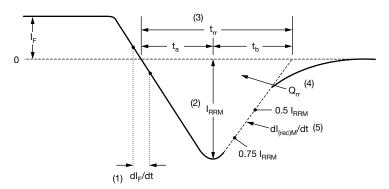


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_{r}$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) $\rm Q_{rr}$ area under curve defined by $\rm t_{rr}$ and $\rm I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

VS-HFA08TB120SPbF

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ORDERING INFORMATION TABLE

Device code

VS-	HF	A	08	ТВ	120	S	TRL	PbF
1	2	3	4	5	6	7	8	9

- 1 HPP product suffix
- 2 HEXFRED® family
- **3** Process designator: A = Electron irradiated
- 4 Current rating (08 = 8 A)
- Package outline (TB = TO-220, 2 leads)
- 6 Voltage rating (120 = 1200 V)
- $7 S = D^2PAK$
- None = Tube (50 pieces)
 - TRL = Tape and reel (left oriented)
 - TRR = Tape and reel (right oriented)
- 9 PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95046</u>					
Part marking information	www.vishay.com/doc?95054				
Packaging information	www.vishay.com/doc?95032				

www.vishay.com

For technical questions, contact: diodestech@vishay.com

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